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EXAMINER

NADAV, ORI

ART UNIT PAPER NUMBER

2811

DATE MAILED: 06/26/2006

Please find below and/or attached an Office communication concerning this application or proceeding.



## DETAILED ACTION

### *Claim Rejections - 35 USC § 103*

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-3, 6, 8, 10, 13 and 15-20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Soininen et al. (6,482,740) in view of Edelstein et al. (6,399,496) and Bogel et al. (6,749,699).

Soininen et al. teach in figure 1 and related text a method of fabricating an integrated circuit, the method comprising:

Depositing an etch stop layer 6 over a first conductive layer 2, wherein the etch stop layer is in direct contact with the first conductive layer;

depositing an insulating layer 8 after the etch stop layer is deposited over the etch stop layer;

forming a barrier layer 14 extending along lateral side walls and a bottom of a via aperture, the via aperture being configured to receive a via material that electrically connects the first conductive layer 2 and a second conductive layer 18; and

depositing/filling a copper 18 alloy (see figure 4 and related text) via material in the via aperture to form a via.

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Soininen et al. do not teach the copper alloy material including Zinc (Zn) or Silver (Ag) and at least one element for increasing grain size including Calcium (Ca) or Chromium (Cr).

Edelstein et al. teach a copper alloy material including Zinc (Zn) or Silver (Ag) and at least one element for increasing grain size including Calcium (Ca) or Chromium (Cr) (column 8, lines 35-52).

Bogel et al. teach that Calcium (Ca) or Chromium (Cr) increases the grain size having one atomic percent or less (column 7, lines 65-67).

It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use a copper alloy material including Zinc (Zn) or Silver (Ag) and at least one element for increasing grain size including Calcium (Ca) or Chromium (Cr) in Soininen et al.'s device in order to provide a stable Cu alloy with improved electromigration properties.

Claims 4 and 22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Soininen et al., Edelstein et al. and Bogel et al., as applied to claim 1 above, and further in view of Merchant et al. (6,440,849).

Regarding claim 4, Soininen et al., Edelstein et al. and Bogel et al. teach substantially the entire claimed structure, as applied to claim 1 above, except the copper alloy via material includes one atomic percent or less of Zinc (Zn) or Silver (Ag).

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Merchant et al. teach the copper alloy via material includes one atomic percent or less of Zinc (Zn) or Silver (Ag) (column 3, lines 6-12).

It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use the copper alloy via material includes one atomic percent or less of Zinc (Zn) or Silver (Ag) in prior art's device in order to provide a stable Cu alloy with improved electromigration properties.

Regarding claim 22, Merchant et al. teach stuffed grain boundaries.

Claims 9 and 23 are rejected under 35 U.S.C. 103(a) as being unpatentable over Soininen et al., Edelstein et al. and Bogel et al., as applied to claims 1 and 6 above, and further in view of Gross (6,380,083).

Soininen et al., Edelstein et al. and Bogel et al. teach substantially the entire claimed structure, as applied to claims 1 and 6 above, except the increased grain size is between 0.5 and 3 microns.

Gross teaches an increased grain size is between 0.5 and 3 microns (column 5, lines 30-36).

It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use an increased grain size is between 0.5 and 3 microns in prior art's device in order to provide a stable Cu alloy with improved electromigration properties.

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Claims 11-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Soininen et al., Edelstein et al. and Bogel et al., as applied to claim 10 above, and further in view of Andricacos et al. (6,090,710).

Soininen et al., Edelstein et al. and Bogel et al. teach substantially the entire claimed structure, as applied to claim 10 above, except the ternary copper alloy via material is at least 98 atomic percent copper and includes Zinc (Zn), Silver (Ag), or Tin (Sn).

Andricacos et al. teach a ternary copper alloy via material is at least 98 atomic percent copper and includes Zinc (Zn), Silver (Ag), or Tin (Sn) (column 8, lines 15-16 and table 1).

It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use a ternary copper alloy via material is at least 98 atomic percent copper and includes Zinc (Zn), Silver (Ag), or Tin (Sn) in prior art's device in order to obtain low resistance copper alloy for vias.

### ***Response to Arguments***

Applicant argues that the examiner's statement that combining the teachings of the references would provide a stable Cu alloy with improved electromigration properties is merely stating an alleged result of the combination and not a motive for the combination.

If the result of combining the references produces a superior device, then this is motivation to an artisan to combine the references.

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Applicant argues that Edelstein et al. do not teach increasing the grain size, and that Bogel et al. do not teach an increase in grain size due to chromium.

Although Edelstein et al. and Bogel et al. do not explicitly state increasing the grain size due to chromium, these features are inherent in prior art's device, because the addition of Calcium (Ca) or Chromium (Cr) increases the grain size.

### ***Conclusion***

**THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than **SIX MONTHS** from the mailing date of this final action.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Ori Nadav whose telephone number is 571-272-1660. The examiner can normally be reached between the hours of 7 AM to 4 PM (Eastern Standard Time) Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



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6/20/06

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